

TO-126 (SOT-32) Plastic Package

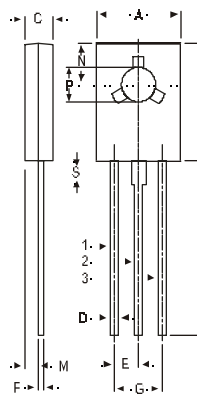
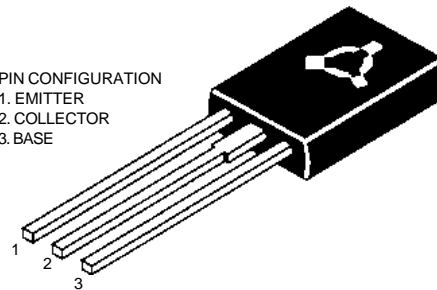
CSC1162

CSC1162 NPN PLASTIC POWER TRANSISTOR

Complementary CSA715

Low frequency Power Amplifier

PIN CONFIGURATION
 1. EMITTER
 2. COLLECTOR
 3. BASE



DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	35 V
Collector-emitter voltage (open base)	V_{CEO}	max.	35 V
Collector current	I_C	max.	2.5 A
Total power dissipation up to $T_C = 25^\circ C$	P_{tot}	max.	10 W
Junction temperature	T_j	max.	150 $^\circ C$
Collector-emitter saturation voltage $I_C = 2A; I_B = 0.2A$	V_{CEsat}	max.	1.0 V
D.C. current gain $I_C = 0.5A; V_{CE} = 2V$	h_{FE}	min.	60
		max.	320

RATINGS (at $T_A=25^\circ C$ unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	V_{CBO}	max.	35 V
Collector-emitter voltage (open base)	V_{CEO}	max.	35 V

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Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V
Collector current	I_C	max.	2.5 A
Collector current (Peak)	I_C	max.	3.0 A
Total power dissipation up to $T_A = 25\text{ }^\circ\text{C}$	P_{tot}	max.	0.75 W
Total power dissipation up to $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	max.	10 W
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Storage temperature	T_{stg}		65 to +150 $^\circ\text{C}$

CHARACTERISTICS

$T_{amb} = 25\text{ }^\circ\text{C}$ unless otherwise specified

Collector cutoff current $I_E = 0; V_{CB} = 35\text{V}$	I_{CBO}	max.	20 μA
Breakdown voltages $I_C = 10\text{ mA}; I_B = 0$	V_{CEO}	min.	35 V
$I_C = 1\text{ mA}; I_E = 0$	V_{CBO}	min.	35 V
$I_E = 1\text{ mA}; I_C = 0$	V_{EBO}	min.	5 V
Saturation voltage $I_C = 2\text{ A}; I_B = 0.2\text{ A}$	V_{CEsat}^*	max.	1.0 V
Base-emitter on voltage $I_C = 1.5\text{A}; V_{CE} = 2\text{V}$ (Pulse)	$V_{BE(on)}$	max.	1.5 V
D.C. current gain $I_C = 0.5\text{ A}; V_{CE} = 2\text{ V}^{**}$	h_{FE}	min.	60
		max.	320
$I_C = 1.5\text{ A}; V_{CE} = 2\text{ V}$ (Pulse)	h_{FE}	min.	20
Transition frequency $I_C = 0.2\text{ A}; V_{CE} = 2\text{ V}$	f_T	typ.	180 MHz

**** h_{FE} classification: B: 60-120 C: 100-200 D: 160-320**

Disclaimer

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